

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of
Hongyong ZHANG et al.

Serial No. 09/726,337

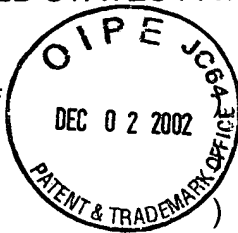
Filed: December 1, 2000

For: A SEMICONDUCTOR DEVICE

CHANNEL FORMATION REGION

COMPRISING SILICON AND

CONTAINING GROUP IV ELEMENT



Art Unit: 2823

Examiner: W. Coleman

#18/0
12/21/02
jim

CERTIFICATE OF MAILING

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AMENDMENT

Honorable Commissioner of Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated August 23, 2002 please amend the above-
identified application as follows:

IN THE CLAIMS:

Please amend claims 2-7 as follows:

2. (Amended) A semiconductor device comprising:
a source region and a drain region;
a channel formation region provided between said source region and said
drain region and provided in a crystalline semiconductor comprising silicon;
wherein said channel formation region comprises an element selected
from group IV elements other than silicon, and
wherein said channel formation region comprises a plurality of crystal
grains provided in said crystalline semiconductor and extending in a same direction.

3. (Amended) A semiconductor device comprising:
a source region and a drain region;

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